Bandgap Engineering of Polycrystalline Ge-doped Sb2Se3 thin-film: Surface and optical properties

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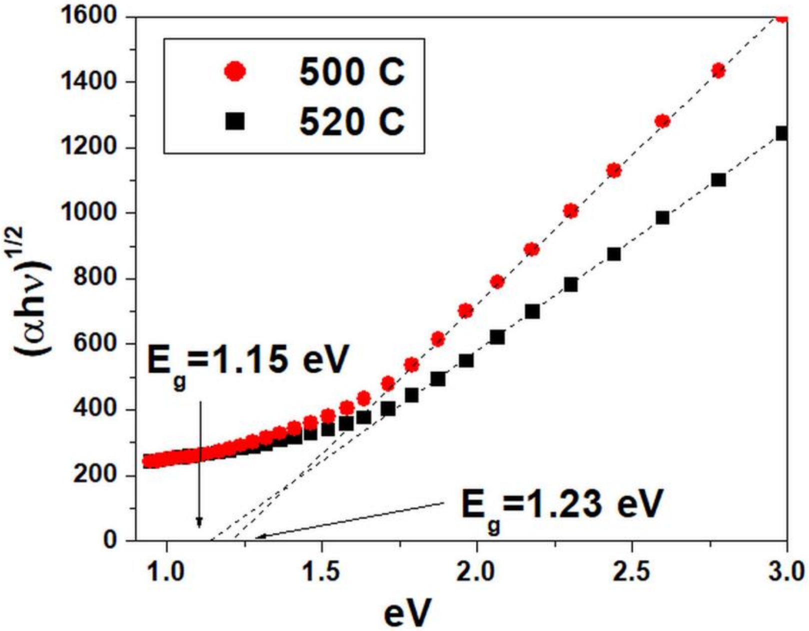

(αhυ)1/2 versus hυ plot for the optical bandgap extraction with linear fitting ($R^2 = 0.99$) of polycrystalline GeSbSe sample at 500 C and 520 C